

## ABSTRACT OF THE DISCLOSURE

A chemical vapor deposition (CVD) method for depositing a silicide and a  
5 CVD system for performing the same are disclosed. A silicide is deposited on a  
substrate. Residual gases remaining from the depositing step are purged out by  
flowing air including  $H_2O$  (g), to substantially remove fumes caused by the residual  
gases. In the purge step, the cycle purge is carried out at the conditions similar to  
the flow of atmosphere, to substantially remove the fumes.

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